

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

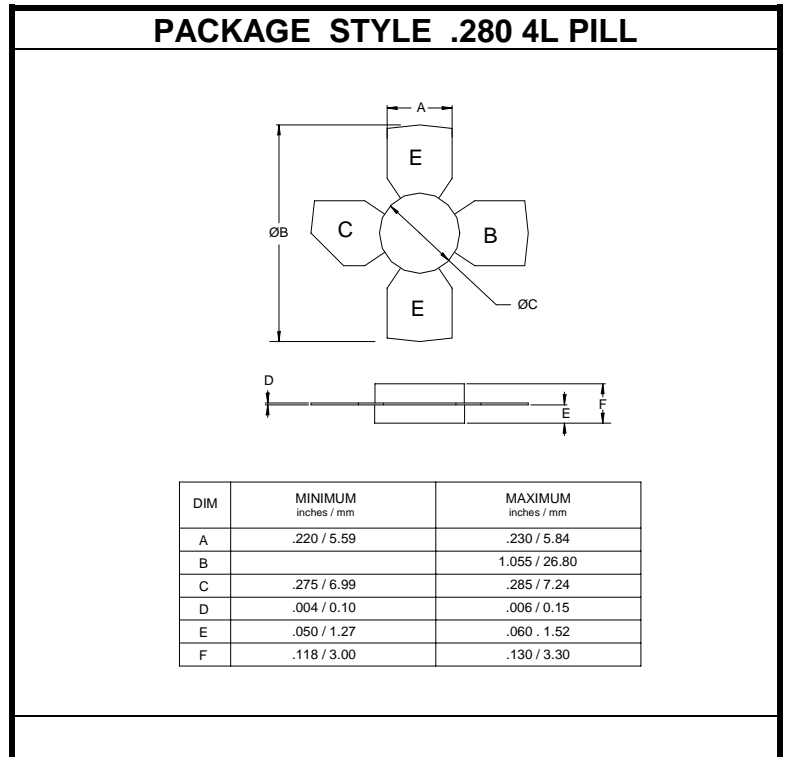
The **ASI MRF652S** is Designed for UHF large signal, amplifier Applications in FM equipment up to 512 MHz.

FEATURES:

- Common Emitter
- $P_G = 10$ dB at 5.0 W/512 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.0 A
V_{CBO}	36 V
V_{CER}	16 V
V_{EBO}	4.0 V
P_{DISS}	25 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	200 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 25$ mA	16			V
BV_{CES}	$I_C = 25$ mA	36			V
BV_{CBO}	$I_C = 25$ mA	36			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CES}	$V_{CE} = 15$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 200$ mA	10		150	---
C_{ob}	$V_{CB} = 15$ V $f = 1.0$ MHz		9.5	15	pF
P_G	$V_{CC} = 12.5$ V $P_{OUT} = 5.0$ W $f = 512$ MHz	10	11		dB
η_c		60	65		%